

MOS FIELD EFFECT TRANSISTOR 2SK3112

SWITCHING N-CHANNEL POWER MOS FET INDUSTRIAL USE

DESCRIPTION

The 2SK3112 is N-channel MOS FET device that features a low on-state resistance and excellent switching characteristics, and designed for high voltage applications such as DC/DC converter, actuator driver.

FEATURES

- Gate voltage rating ± 30 V
- Low on-state resistance
 $R_{DS(on)} = 110 \text{ m}\Omega \text{ MAX. (} V_{GS} = 10 \text{ V, } I_D = 13 \text{ A)}$
- Low input capacitance
 $C_{iss} = 1600 \text{ pF TYP. (} V_{DS} = 10 \text{ V, } V_{GS} = 0 \text{ V)}$
- Avalanche capability rated
- Built-in gate protection diode
- Surface mount device available

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

Drain to Source Voltage ($V_{GS} = 0 \text{ V}$)	V_{DSS}	200	V
Gate to Source Voltage ($V_{DS} = 0 \text{ V}$)	V_{GSS}	± 30	V
Drain Current (DC) ($T_C = 25^\circ\text{C}$)	$I_{D(DC)}$	± 25	A
Drain Current (pulse) ^{Note1}	$I_{D(pulse)}$	± 75	A
Total Power Dissipation ($T_C = 25^\circ\text{C}$)	P_{T1}	100	W
Total Power Dissipation ($T_A = 25^\circ\text{C}$)	P_{T2}	1.5	W
Channel Temperature	T_{ch}	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$
Single Avalanche Current ^{Note2}	I_{AS}	25	A
Single Avalanche Energy ^{Note2}	E_{AS}	250	mJ

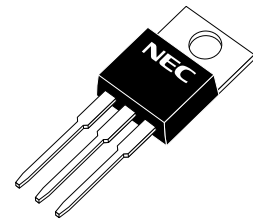
Notes 1. $PW \leq 10 \mu\text{s}$, Duty Cycle $\leq 1\%$

2. Starting $T_{ch} = 25^\circ\text{C}$, $V_{DD} = 100 \text{ V}$, $R_G = 25 \Omega$, $V_{GS} = 20 \text{ V} \rightarrow 0 \text{ V}$

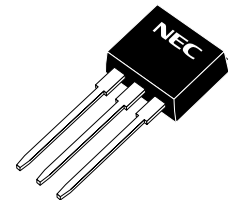
ORDERING INFORMATION

PART NUMBER	PACKAGE
2SK3112	TO-220AB
2SK3112-S	TO-262
2SK3112-ZJ	TO-263(MP-25ZJ)

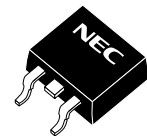
(TO-220AB)



(TO-262)



(TO-263)

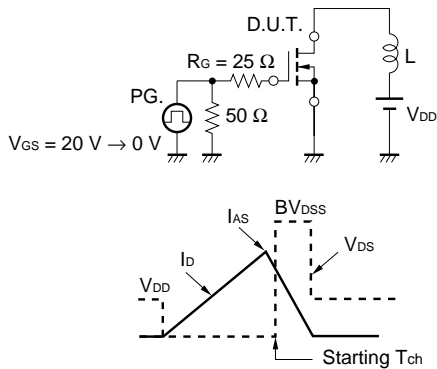


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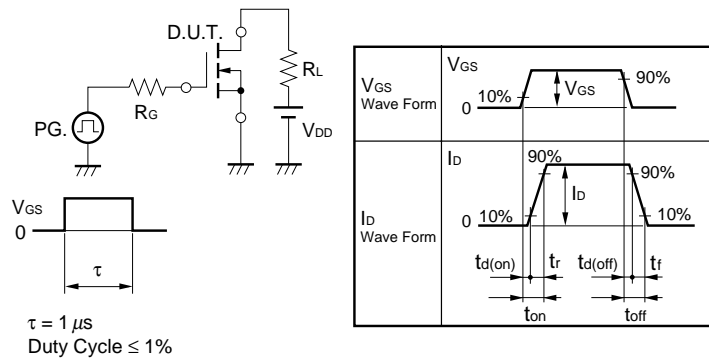
ELECTRICAL CHARACTERISTICS (T_A = 25°C)

Characteristics	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 200 V, V _{GS} = 0 V			100	μA
Gate Leakage Current	I _{GSS}	V _{GS} = ±30 V, V _{DS} = 0 V			±10	μA
Gate Cut-off Voltage	V _{GS(off)}	V _{DS} = 10 V, I _D = 1 mA	2.5		4.5	V
Forward Transfer Admittance	y _{fs}	V _{DS} = 10 V, I _D = 13 A	6.0			S
Drain to Source On-state Resistance	R _{DS(on)}	V _{GS} = 10 V, I _D = 13 A		76	110	mΩ
Input Capacitance	C _{iss}	V _{DS} = 10 V		1600		pF
Output Capacitance	C _{oss}	V _{GS} = 0 V		430		pF
Reverse Transfer Capacitance	C _{rss}	f = 1 MHz		280		pF
Turn-on Delay Time	t _{d(on)}	V _{DD} = 100 V, I _D = 13 A		35		ns
Rise Time	t _r	V _{GS} = 10 V		140		ns
Turn-off Delay Time	t _{d(off)}	R _G = 10 Ω		110		ns
Fall Time	t _f			70		ns
Total Gate Charge	Q _G	V _{DD} = 160 V		60		nC
Gate to Source Charge	Q _{GS}	V _{GS} = 10 V		11		nC
Gate to Drain Charge	Q _{GD}	I _D = 25 A		40		nC
Body Diode Forward Voltage	V _{F(S-D)}	I _F = 25 A, V _{GS} = 0 V		1.0		V
Reverse Recovery Time	t _{rr}	I _F = 25 A, V _{GS} = 0 V		300		ns
Reverse Recovery Charge	Q _{rr}	di/dt = 50 A/μs		1.8		μC

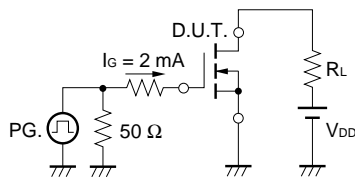
TEST CIRCUIT 1 AVALANCHE CAPABILITY



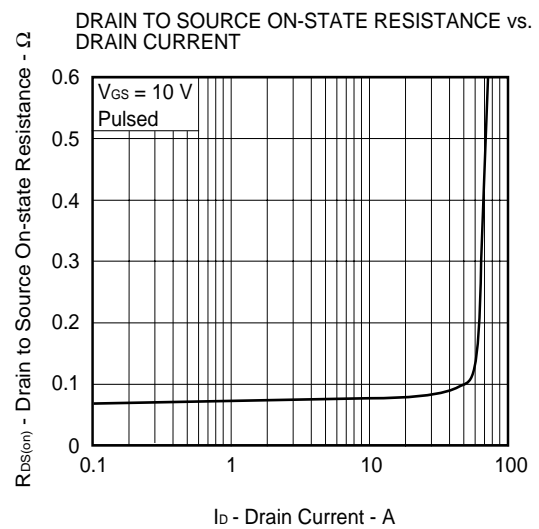
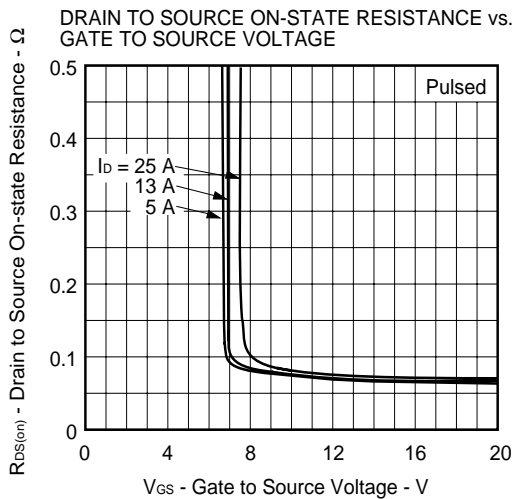
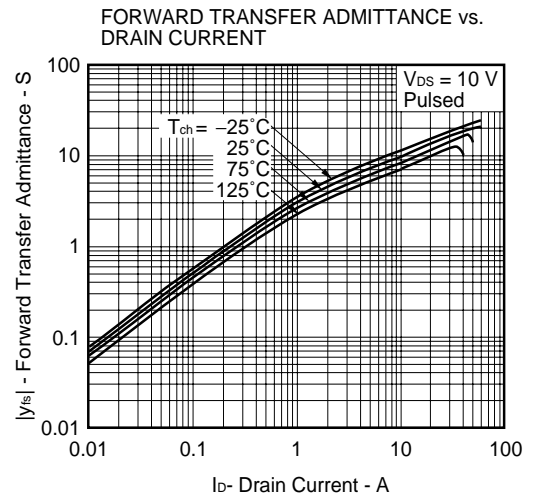
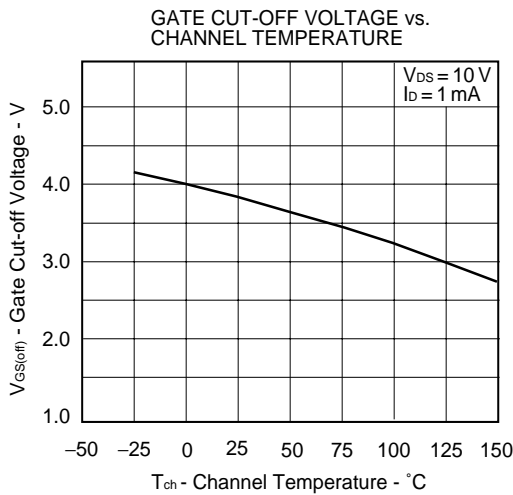
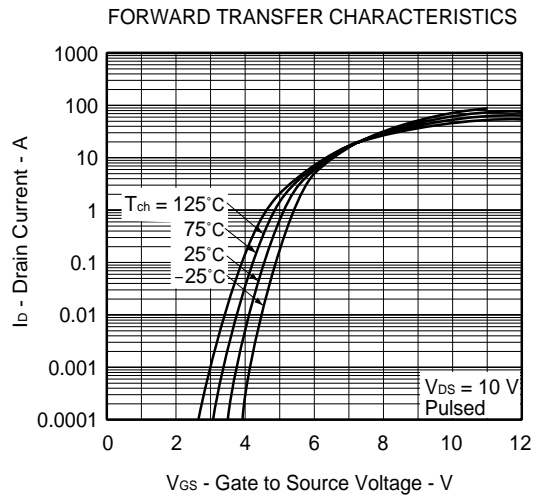
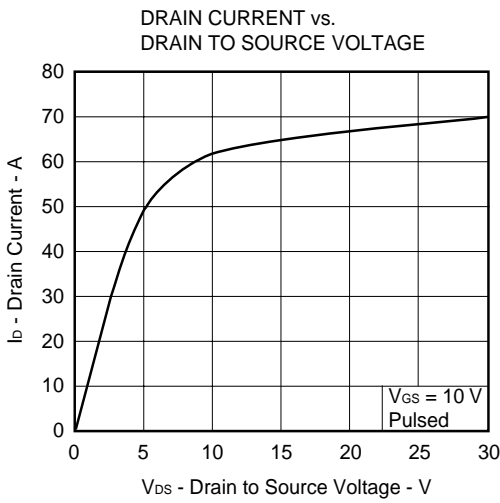
TEST CIRCUIT 2 SWITCHING TIME

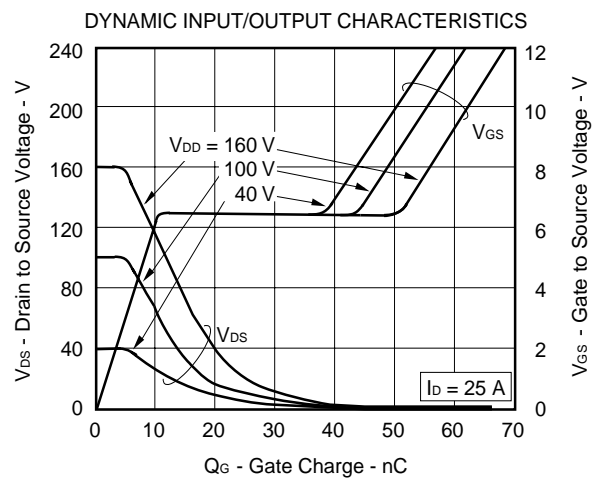
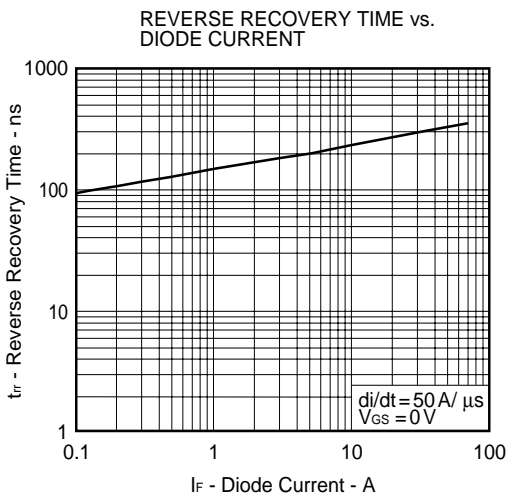
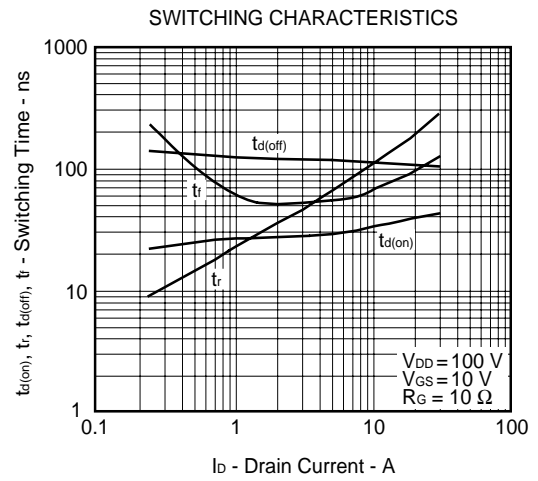
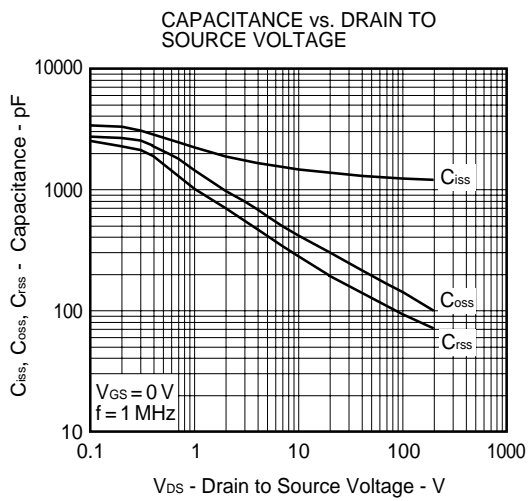
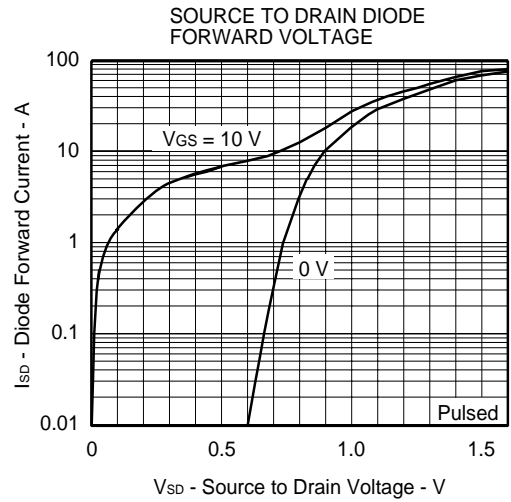
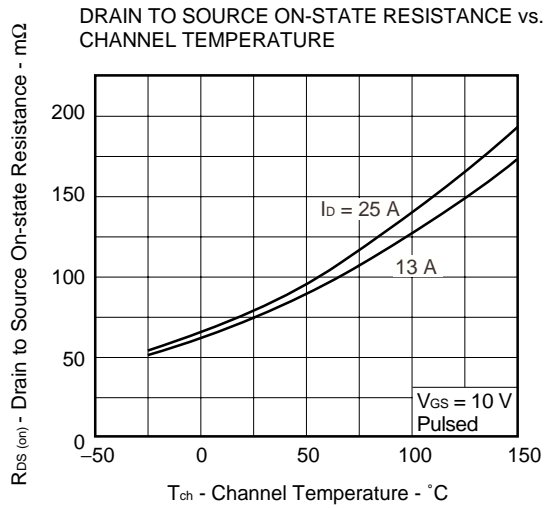


TEST CIRCUIT 3 GATE CHARGE

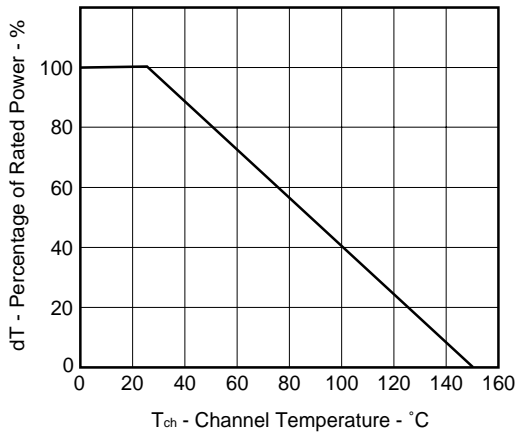


TYPICAL CHARACTERISTICS (T_A = 25°C)

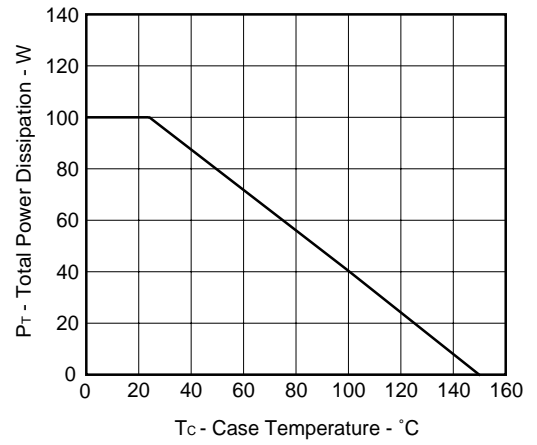




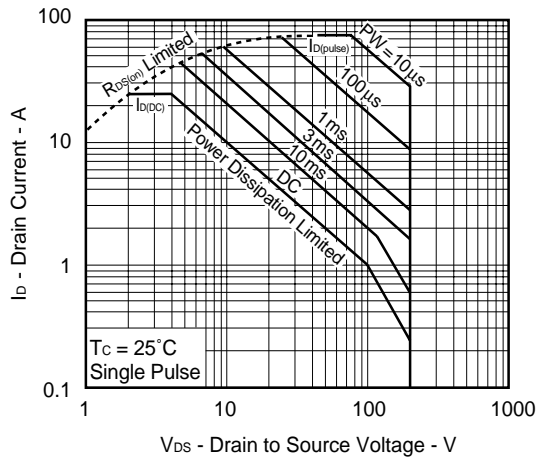
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



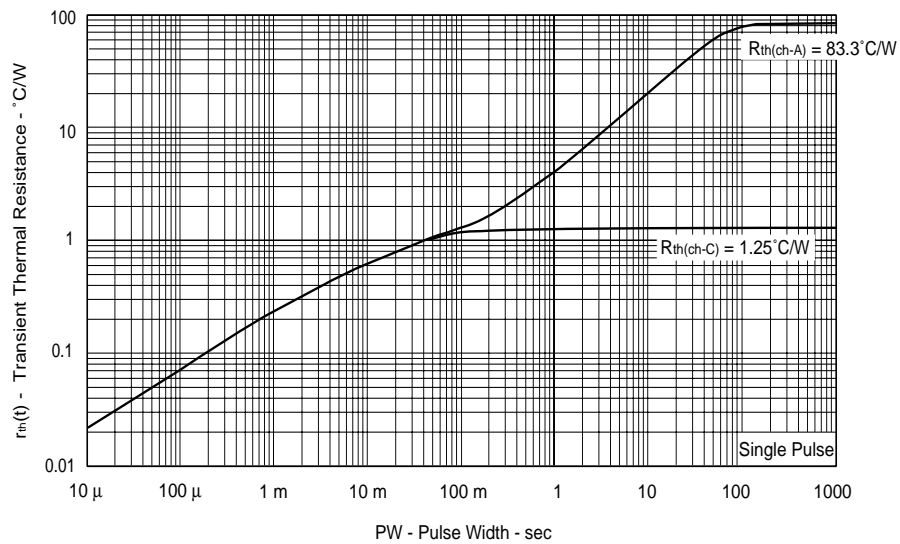
TOTAL POWER DISSIPATION vs. CASE TEMPERATURE

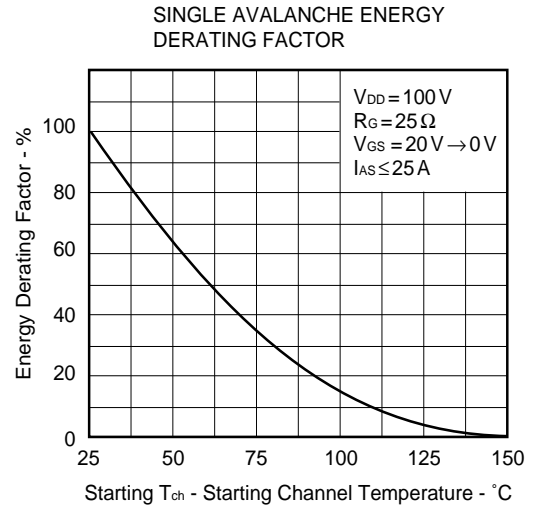
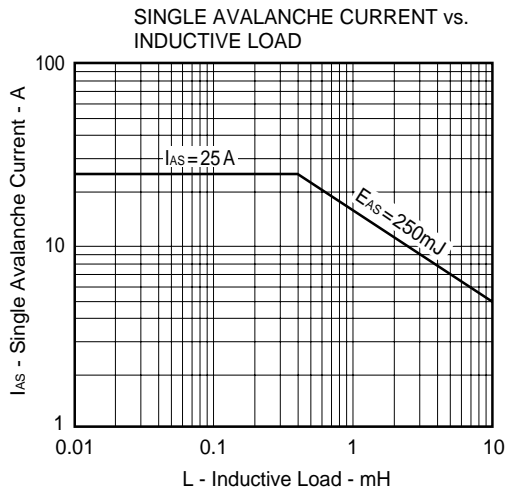


FORWARD BIAS SAFE OPERATING AREA



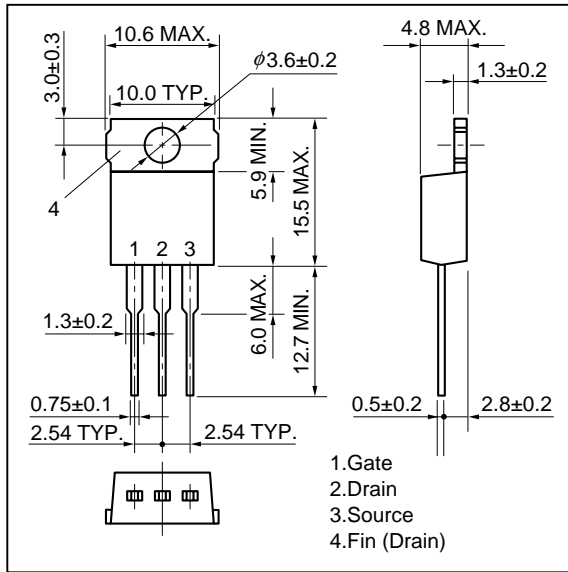
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



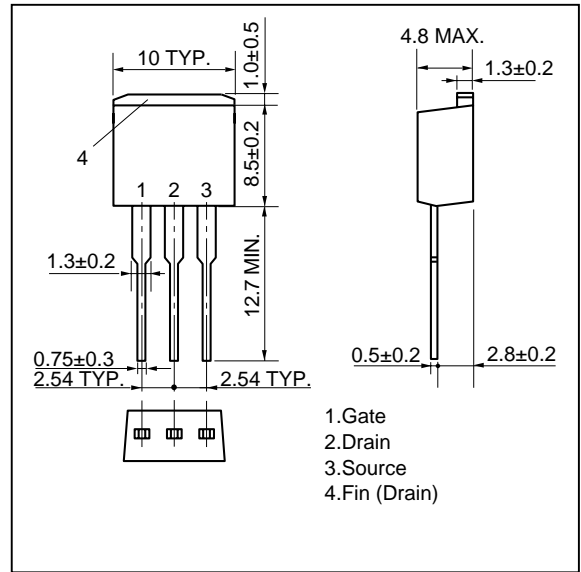


PACKAGE DRAWINGS (Unit : mm)

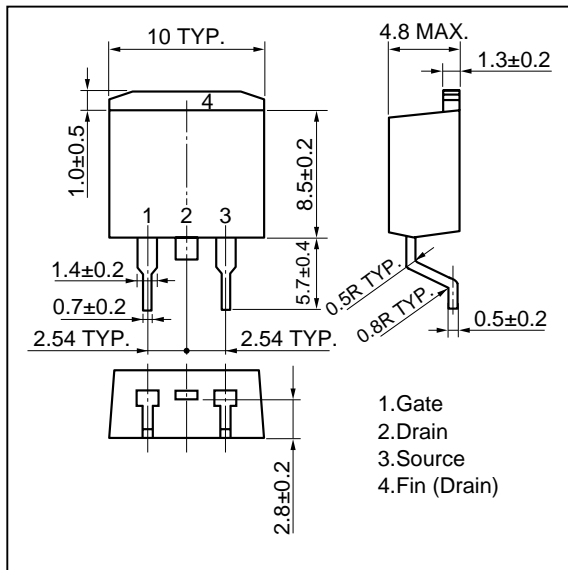
1)TO-220AB (MP-25)



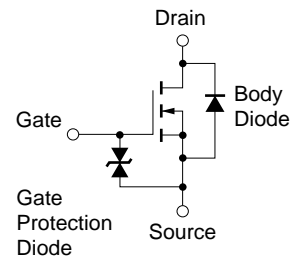
2)TO-262



3)TO-263 (MP-25ZJ)



EQUIVALENT CIRCUIT



Remark The diode connected between the gate and source of the transistor serves as a protector against ESD.

When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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